L Number	Hits	Search Text	DB	Time stamp
1	0	(silicon or polysilicon) same (pascal or MPa) same (residual adj stress) same (pores or porous or porosity) same (grain or grains)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 09:53
2	3	(silicon or polysilicon) same (pascal or MPa) same (residual adj stress) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 13:19
3	4	("5596219" "5789753" "5830372" "6194722").PN.	USPAT	2004/01/05
4	23	(silicon or polysilicon) same (grain or grains) same (hemispherical or sperical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05
5	0	(silicon or polysilicon) same membrane same (grain or grains) same (hemispherical or sperical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 13:51
6	0	(silicon or polysilicon) same membrane same (grain or grains) same (hemispherical or spherical) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 13:51
7	13	(silicon or polysilicon) same membrane same (grain or grains) same (pores or porous or porosity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 14:59
8	3667	((438/1-4) or (438/22-29)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 14:59
9	29	(((438/1-4) or (438/22-29)).CCLS.) and (silicon with membrane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 14:59
10	0	((((438/1-4) or (438/22-29)).CCLS.) and (silicon with membrane)) and (residual adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 15:00
11	26	(((438/1-4) or (438/22-29)).CCLS.) and (residual adj stress)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/05 15:14
12	0	(((438/1-4) or (438/22-29)).CCLS.) and ((residual adj stress) same (MPa or pascals))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 15:16
13	0	(((438/1-4) or (438/22-29)).CCLS.) and ((residual adj stress) same (Pa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/05 15:16
_	2	semiconductor and substrate and "SiO.sub.2" and "SiN" and (porous same grain\$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/31

	154	semiconductor and substrate and	USPAT;	2003/01/22
-	134	"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	13:34
		(polysilicon or (polycrystalline with	EPO; JPO;	15.54
			DERWENT;	
		silicon)))		
		3 3 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	IBM_TDB	2002 (01 (22
_	0	semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	10:42
		monolayer same (polysilicon or	EPO; JPO;	
		(polycrystalline with silicon)))	DERWENT;	
			IBM_TDB	
-	0	semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	10:43
		(monomolecular adj layer) same	EPO; JPO;	
		(polysilicon or (polycrystalline with	DERWENT;	
		silicon)))	IBM TDB	
_	5	semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	10:50
		(thin adj layer) same (polysilicon or	EPO; JPO;	
		(polycrystalline with silicon)))	DERWENT;	
		(polyolyboullane with billion,,,	IBM TDB	
	0	semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	10:50
		(membrane) same (polysilicon or	EPO; JPO;	10.30
			DERWENT;	
		(polycrystalline with silicon)))	IBM TDB	
	154	gomiganduaton and substrate	_	2002/01/22
-	154	semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	13:34
		(polysilicon or (polycrystalline with	EPO; JPO;	
		silicon)))	DERWENT;	
			IBM_TDB	
-	28	(semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	13:41
İ		(polysilicon or (polycrystalline with	EPO; JPO;	<u> </u>
İ		silicon)))) and filter	DERWENT;	1
			IBM_TDB	
-	0	(semiconductor and substrate and	USPAT;	2003/01/22
İ		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	13:42
		(polysilicon or (polycrystalline with	EPO; JPO;	
		silicon)))) and (sacrificial with	DERWENT;	1
		layer) and HF	IBM_TDB	1
-	5	(semiconductor and substrate and	USPAT;	2003/01/22
		"SiO.sub.2" and "SiN" and (grain\$1 same	US-PGPUB;	15:45
		(polysilicon or (polycrystalline with	EPO; JPO;	1
		silicon)))) and (sacrificial with	DERWENT;	
		layer)	IBM TDB	
-	0	semiconductor and (micromachined with	USPAT;	2003/01/22
1		encapsulation) and (permeable with	US-PGPUB;	15:46
		polysilicon) and HF	EPO; JPO;	
			DERWENT;]
			IBM TDB	
-	0	semiconductor and (micromachined with	USPAT;	2003/01/22
		encapsulation) and (polysilicon) and HF	US-PGPUB;	15:46
		porjorranding and in	EPO; JPO;	
			DERWENT;	
	-		IBM TDB	
1_	183	 semiconductor and (micromachined) and	USPAT;	2003/01/22
-	103			15:47
		(polysilicon) and HF	US-PGPUB;	13.47
			EPO; JPO;	
			DERWENT;	
		/	IBM_TDB	2002/01/22
-	0	(semiconductor and (micromachined) and	USPAT;	2003/01/22
		(polysilicon) and HF) and SiO and SiN	US-PGPUB;	15:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	24	(semiconductor and (micromachined) and	USPAT;	2003/01/22
		(polysilicon) and HF) and SiN	US-PGPUB;	15:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			Transa	2002/01/20
-	22	((semiconductor and (micromachined) and	USPAT;	2003/01/22
		(polysilicon) and HF) and SiN) and oxide	US-PGPUB; EPO; JPO;	15:56
				1
			DERWENT;	
1	1.0	 Lebouitz.in.	IBM_TDB USPAT;	2003/01/22
-	19	Lebouitz.in.	US-PGPUB;	15:56
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
	8	Lebouitz.in. and polysilicon	USPAT;	2003/01/22
		perodicz.iii. and porysirioon	US-PGPUB;	15:57
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	8	(Lebouitz.in. and polysilicon) and oxide	USPAT;	2003/01/22
			US-PGPUB;	15:57
			EPO; JPO;	1
			DERWENT;	
1			IBM_TDB	0000 /01 /00
-	8	((Lebouitz.in. and polysilicon) and	USPAT;	2003/01/22
		oxide) and nitride	US-PGPUB;	15:57
			EPO; JPO;	
			DERWENT; IBM TDB	
	1.0	17190101	USPAT;	2003/01/23
_	10	"718010"	US-PGPUB	13:14
	6	(("5919364") or ("5651900") or	USPAT;	2003/01/24
_		("4801380")).PN.	US-PGPUB;	22:32
		(.501500 //	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3		USPĀT	2003/01/24
		("4801380")).PN.		22:32
_	658	(silicon or Si) with (residual with	USPAT;	2003/12/31
		stress)	US-PGPUB;	13:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/12/21
_	54	((silicon or Si) with (residual with	USPAT;	2003/12/31 11:08
		stress)) with (Pa or pascals or MPa)	US-PGPUB; EPO; JPO;	11:00
			DERWENT;	
			IBM TDB	
	18	(US-5949570-\$ or US-5920418-\$ or	USPAT;	2003/12/31
-	18	US-5894452-\$ or US-5878105-\$ or	JPO;	11:08
		US-5744378-\$ or US-6663973-\$ or	DERWENT	
	1	US-6622373-\$ or US-6610815-\$ or		
		US-6489066-\$ or US-6396900-\$ or		
		US-6383317-\$ or US-6359276-\$ or		
		US-6342333-\$ or US-6072620-\$).did. or		
		(JP-2002038260-\$).did. or		
		(JP-2001214055-\$ or JP-06305862-\$ or		
		JP-06305861-\$).did.		
-	0		USPAT;	2003/12/31
	1	US-5894452-\$ or US-5878105-\$ or	US-PGPUB;	11:08
		US-5744378-\$ or US-6663973-\$ or	EPO; JPO;	
		US-6622373-\$ or US-6610815-\$ or	DERWENT;	
		US-6489066-\$ or US-6396900-\$ or	IBM_TDB	
		US-6383317-\$ or US-6359276-\$ or		
1		US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or		
		(JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or		
		JP-06305861-\$).did.) and sacrificia		
L		or occording the and sacrificat		

Table	12/31
US-5744378-\$ or US-6663973-\$ or US-6622373-\$ or US-6610815-\$ or US-6489066-\$ or US-6396900-\$ or US-6383317-\$ or US-6372620-\$ or US-6342333-\$ or US-6072620-\$ or US-6342333-\$ or US-6072620-\$ or US-6342333-\$ or US-6072620-\$ or US-6342333-\$ or US-6072620-\$ or US-6305861-\$ or UJP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$ or JP-06305862-\$ or JP-06305861-\$ or JP-06305862-\$ or JP-06305861-\$ or JP-06305862-\$ or JP-06305861-\$ or JP-06305862-\$ or JP-06305862-\$ or JP-06305862-\$ or JP-06305861-\$ or JP-06305862-\$ or JP-	12/31
US-6622373-\$ or US-6610815-\$ or US-6489066-\$ or US-6396900-\$ or US-6383317-\$ or US-6359276-\$ or US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial - 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 (Silicon or Si) with (residual with stress)) and (grain with pores with membrane)	
US-6622373-\$ or US-6610815-\$ or US-6489066-\$ or US-6396900-\$ or US-6383317-\$ or US-6359276-\$ or US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial - 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 (Silicon or Si) with (residual with stress)) and (grain with pores with membrane)	
US-6489066-\$ or US-6396900-\$ or US-6383317-\$ or US-6359276-\$ or US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial - 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB uspat; US-PGPUB; EPO; JPO; DERWENT; U	
US-6383317-\$ or US-6359276-\$ or US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) and filter 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 (Silicon or Si) with (residual with stress)) and (grain with pores with us-pgpuB; membrane) 1 (Silicon or Si) with (residual with stress) year (US-pgpuB; membrane)	
US-6342333-\$ or US-6072620-\$).did. or (JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) (USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	
(JP-2002038260-\$).did. or (JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) and filter (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (US-PGPUB; EPO; JPO; IS-PGPUB; IS-	
(JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) (USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EFO; JPO; DERWENT; US-PGPUB; EFO; JPO;	
(JP-2001214055-\$ or JP-06305862-\$ or JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) (USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EFO; JPO; DERWENT; US-PGPUB; EFO; JPO;	
JP-06305861-\$).did.) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial ((silicon or Si) with (residual with stress)) and sacrificial) ((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) JP-06305861-\$).did.) and sacrificial USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	
- 64 ((silicon or Si) with (residual with stress)) and sacrificial US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (((silicon or Si) with (residual with stress)) and sacrificial) and filter US-PGPUB; EPO; JPO; DERWENT; IBM_TDB ((silicon or Si) with (residual with stress)) and (grain with pores with stress)) and (grain with pores with membrane) ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) (USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;	
stress)) and sacrificial 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO;	
PO; JPO; DERWENT; IBM_TDB (((silicon or Si) with (residual with stress)) and sacrificial) and filter ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/1 USPAT; 2003/1 US-PGPUB; 13:20	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; Stress)) and (grain with pores with membrane) US-PGPUB; EPO; JPO;	12/31
- 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	12/31
- 9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	12/31
9 (((silicon or Si) with (residual with stress)) and sacrificial) and filter 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 9 (((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 1 ((silicon or Si) with (residual with stress)) and (grain with pores with membrane) 2003/3 11:09 EPO; JPO;	12/31
stress)) and sacrificial) and filter US-PGPUB; EPO; JPO; DERWENT; IBM_TDB ((silicon or Si) with (residual with Stress)) and (grain with pores with WS-PGPUB; BY-PGPUB; Membrane) US-PGPUB; STREST,	TC/2T
EPO; JPO; DERWENT; IBM_TDB ((silicon or Si) with (residual with USPAT; 2003/: stress)) and (grain with pores with US-PGPUB; membrane) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; 13:20	
DERWENT; IBM_TDB USPAT; stress)) and (grain with pores with membrane) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	
1 ((silicon or Si) with (residual with USPAT; 2003/1 stress)) and (grain with pores with EPO; JPO; 13:20	
1 ((silicon or Si) with (residual with USPAT; 2003/1 stress)) and (grain with pores with EPO; JPO; 13:20	
- 1 ((silicon or Si) with (residual with USPAT; 2003/: stress)) and (grain with pores with US-PGPUB; 13:20 membrane) EPO; JPO;	
stress)) and (grain with pores with US-PGPUB; 13:20 membrane) EPO; JPO;	12/31
membrane) EPO; JPO;	
I DECARDITY I	
IBM TDB	
	12/31
stress)) and (grain with pore\$1 with US-PGPUB; 13:20	
membrane) EPO; JPO;	
DERWENT;	
IBM TDB	
i i — I	12/21
1 //02220011 02 02/ 12020 /2002011 11	
stress)) and (grain with pore\$1) US-PGPUB; 13:20	
EPO; JPO;	
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	10/01
2 ((silicon or Si) with (residual with USPAT; 2003/	
stress)) and (grain\$1 with pore\$1) US-PGPUB; 13:21	
EPO; JPO;	
DERWENT;	
IBM TDB	
	12/21
/ / / DITION OF DI/ WITH / I DOWN WHITH !!!	
stress)) and (membrane with pore\$1) US-PGPUB; 13:27	
EPO; JPO;	
DERWENT;	
IBM TDB	
	12/31
Z (Sificon of Si / With /Its Adda with Its	
stress)) and (membrane with porosity) US-PGPUB; 13:37	
EPO; JPO;	
DERWENT;	
IBM TDB	
	12/31
J (0110313 /:111:	•
US-PGPUB; 13:55	
EPO; JPO;	
DERWENT;	
IBM TDB	
	12/31
12 1000120 2010120	
"4966646" "5068203" "5177579" 13:37	1
"5178015" "5348617" "5622633"	
"5627396" "5725729" "5804462").PN.	
	12/31
14 5622633. URPN. 13:45	
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
- 73 4740410.URPN. USPAT 2003/	
13:46)
13:46	, 12/31
13:46 - 4808 ((438/764) or (438/767) or (438/694) or USPAT; 2003/	12/31
- 4808 ((438/764) or (438/767) or (438/694) or USPAT; 2003/ (210/321.84) or (210/500.25) or US-PGPUB; 13:56	12/31
- 4808 ((438/764) or (438/767) or (438/694) or USPAT; 2003/ (210/321.84) or (210/500.25) or US-PGPUB; 13:56 (210/500.26) or (156/625.1)).CCLS.	12/31
- 4808 ((438/764) or (438/767) or (438/694) or USPAT; 2003/ (210/321.84) or (210/500.25) or US-PGPUB; 13:56	12/31

-	255	(((438/764) or (438/767) or (438/694) or	USPAT;	2003/12/31
		(210/321.84) or (210/500.25) or	US-PGPUB;	13:57
1		(210/500.26) or (156/625.1)).CCLS.) and	EPO; JPO;	
		@PD>20030122	DERWENT;	
			IBM_TDB	
-	0		USPAT;	2003/12/31
		(210/321.84) or (210/500.25) or	US-PGPUB;	13:57
		(210/500.26) or (156/625.1)).CCLS.) and	EPO; JPO;	
		<pre>@PD>20030122) and (residual with stress)</pre>	DERWENT;	
			IBM_TDB	
_	11		USPAT;	2003/12/31
		(210/321.84) or (210/500.25) or	US-PGPUB;	14:09
		(210/500.26) or (156/625.1)).CCLS.) and	EPO; JPO;	
		(residual with stress)	DERWENT;	
			IBM_TDB	((
-	4337		USPAT;	2003/12/31
		or (427/452) or (427/563) or (427/567) or	US-PGPUB;	14:10
		(427/574) or (427/578) or (427/588) or	EPO; JPO;	
		(438/647) or (438/657) or (438/684) or	DERWENT;	
		(438/719) or (438/753)).CCLS.	IBM_TDB	
-	29		USPAT;	2003/12/31
		or (427/452) or (427/563) or (427/567) or	US-PGPUB;	14:41
		(427/574) or (427/578) or (427/588) or	EPO; JPO;	
		(438/647) or (438/657) or (438/684) or	DERWENT;	
		(438/719) or (438/753)).CCLS.) and	IBM_TDB	
		(residual with stress)		